

SPECIFICATION

Device Name : Power Integrated Module

Type Name : 7MBR100U4B120

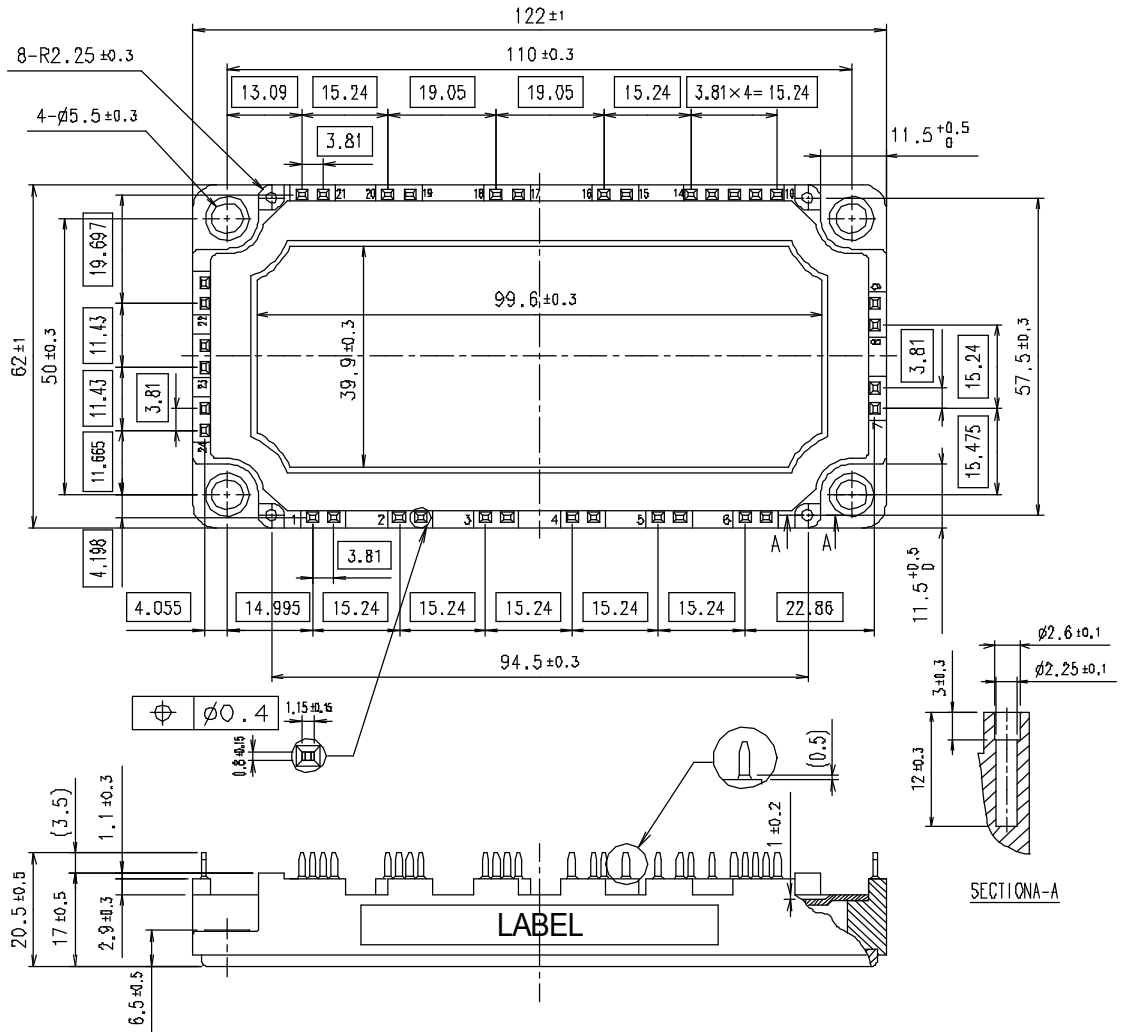
Spec. No. : MS6M 0856

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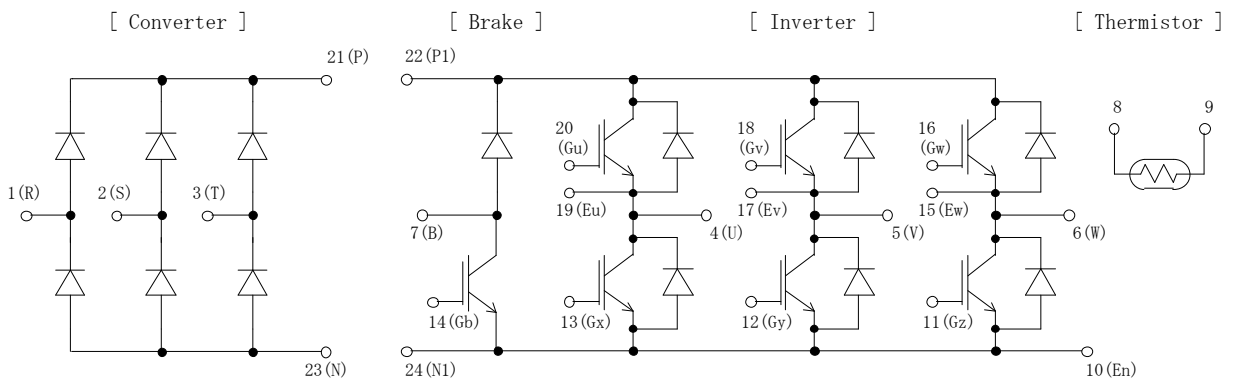
7MBR100U4B120

1. Outline Drawing (Unit : mm)



shows theoretical dimension.
 () shows reference dimension.

2. Equivalent circuit



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3. Absolute Maximum Ratings (at Tc= 25°C unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units	
Inverter	Collector-Emitter voltage	VCES		1200	V	
	Gate-Emitter voltage	VGES		±20	V	
	Collector current	Ic	Continuous	Tc=25°C	100	A
				Tc=80°C	75	
		Icp	1ms	Tc=25°C	200	
				Tc=80°C	150	
		-Ic			100	
-Ic pulse	1ms		200			
Collector Power Dissipation	Pc	1 device		390	W	
Brake	Collector-Emitter voltage	VCES		1200	V	
	Gate-Emitter voltage	VGES		±20	V	
	Collector current	Ic	Continuous	Tc=25°C	50	A
				Tc=80°C	35	
		Icp	1ms	Tc=25°C	100	
				Tc=80°C	70	
Collector Power Dissipation	Pc	1 device		205	W	
Repetitive peak reverse Voltage (Diode)	VRRM			1200	V	
Converter	Repetitive peak reverse Voltage	VRRM		1600	V	
	Average Output Current	Io	50Hz/60Hz sine wave	100	A	
	Surge Current (Non-Repetitive)	IFSM	Tj=150°C, 10ms	520	A	
	I ² t (Non-Repetitive)	I ² t	half sine wave	1352	A ² s	
Junction temperature	Tj		150	°C		
Storage temperature	Tstg		-40 ~ +125			
Isolation voltage	between terminal and copper base (*1)	Viso	AC : 1min.	2500	VAC	
	between thermistor and others (*2)					
Screw Torque	Mounting (*3)	-		3.5	N m	

(*1) All terminals should be connected together when isolation test will be done.

(*2) Two thermistor terminals should be connected together, each other terminals should be connected together and shorted to base plate when isolation test will be done.

(*3) Recommendable Value : 2.5~3.5 Nm (M5)

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4. Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
Inverter	Zero gate voltage Collector current	ICES	VGE = 0V VCE = 1200V	-	-	1.0	mA	
	Gate-Emitter leakage current	IGES	VCE = 0V VGE=±20V	-	-	200	nA	
	Gate-Emitter threshold voltage	VGE(th)	VCE = 20V Ic = 100mA	4.5	6.5	8.5	V	
	Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V Ic = 100A	Tj= 25°C	-	2.60	2.85	V
				Tj=125°C	-	2.95	-	
		VCE(sat) (chip)	Tj= 25°C	-	2.10	2.35		
			Tj=125°C	-	2.45	-		
	Input capacitance	Cies	VCE=10V, VGE=0V, f=1MHz	-	8	-	nF	
	Turn-on time	ton	Vcc = 600V	-	0.38	1.20	μs	
		tr	Ic = 100A	-	0.13	0.60		
		tr (i)	VGE=±15V	-	0.03	-		
	Turn-off time	toff	Rg = 9.1 Ω	-	0.41	1.00	μs	
		tf		-	0.07	0.30		
Forward on voltage	VF (terminal)	VGE=0V IF = 100A	Tj= 25°C	-	2.60	2.85	V	
			Tj=125°C	-	2.90	-		
	VF (chip)	Tj= 25°C	-	2.10	2.35			
		Tj=125°C	-	2.40	-			
Reverse recovery time	trr	IF = 100A	-	-	0.35	μs		
Brake	Zero gate voltage Collector current	ICES	VGE = 0V VCE = 1200V	-	-	1.0	mA	
	Gate-Emitter leakage current	IGES	VCE = 0V VGE=±20V	-	-	200	nA	
	Collector-Emitter saturation voltage	VCE(sat) (terminal)	VGE=15V Ic = 50A	Tj= 25°C	-	2.25	2.65	V
				Tj=125°C	-	2.60	-	
		VCE(sat) (chip)	Tj= 25°C	-	2.00	2.40		
			Tj=125°C	-	2.35	-		
	Turn-on time	ton	Vcc = 600V	-	0.53	1.20	μs	
		tr	Ic = 50A	-	0.43	0.60		
toff		VGE=±15V	-	0.37	1.00			
Turn-off time	tf	Rg = 33 Ω	-	0.07	0.30	μs		
	Reverse current	IRRM	VR=1200V	-	-	1.0	mA	
Converter	Forward on voltage	VFM	VGE=0V	terminal	-	1.55	1.90	V
			IF = 100A	chip	-	1.40	-	
Reverse current	IRRM	VR=1600V	-	-	1.0	mA		
Thermistor	Resistance	R	T = 25°C	-	5000	-	Ω	
			T = 100°C	465	495	520		
	B value	B	T = 25/50°C	3305	3375	3450	K	

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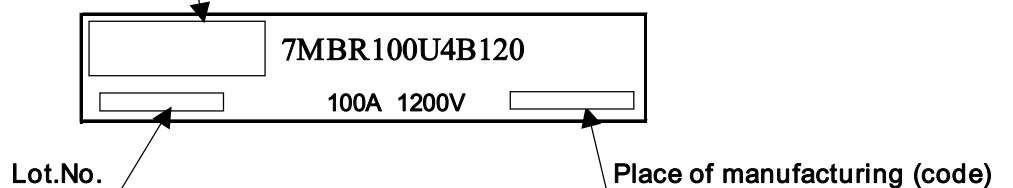
5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance(1device)	Rth(j-c)	Inverter IGBT	-	-	0.32	°C/W
		Inverter FWD	-	-	0.58	
		Brake IGBT	-	-	0.60	
		Converter Diode	-	-	0.50	
Contact Thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.05	-	

(*4) This is the value which is defined mounting on the additional cooling fin with thermal compound.

6. Indication on module

Logo of production



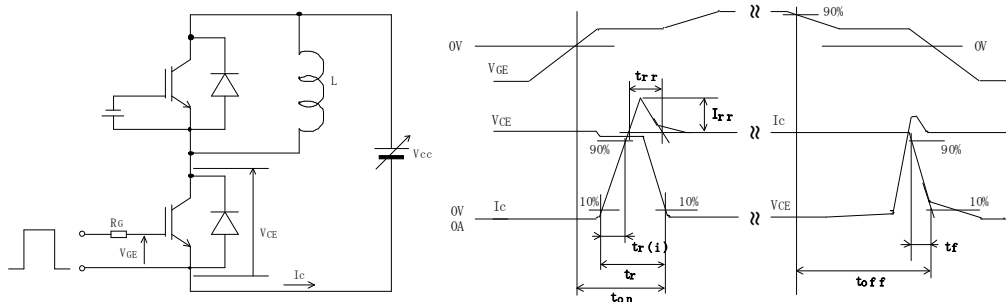
7.Applicable category

This specification is applied to Power Integrated Module named 7MBR100U4B120 .

8.Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.

9. Definitions of switching time



10. Packing and Labeling

- Display on the packing box
- Logo of production
 - Type name
 - Lot No
 - Products quantity in a packing box